

# MOSFET – P-Channel, QFET® -100 V, -16.5 A, 190 mΩ

## FQP17P10

This P-Channel enhancement mode power MOSFET is produced using onsemi's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- -16.5 A, -100 V,  $R_{DS(on)}$  = 190 mΩ (Max.) at  $V_{GS} = -10$  V,  $I_D = -8.25$  A
- Low Gate Charge (Typ. 30 nC)
- Low  $C_{rss}$  (Typ. 100 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating
- This is a Pb-Free Device

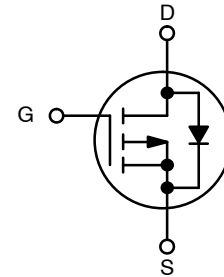
### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

| Symbol         | Parameter                                                            |                                          | Ratings     | Unit             |
|----------------|----------------------------------------------------------------------|------------------------------------------|-------------|------------------|
| $V_{DSS}$      | Drain-Source Voltage                                                 |                                          | -100        | V                |
| $I_D$          | Drain Current                                                        | Continuous ( $T_C = 25^\circ\text{C}$ )  | -16.5       | A                |
|                |                                                                      | Continuous ( $T_C = 100^\circ\text{C}$ ) | -11.7       |                  |
| $I_{DM}$       | Drain Current                                                        | Pulsed (Note 1)                          | -66         | A                |
| $V_{GSS}$      | Gate-Source Voltage                                                  |                                          | $\pm 30$    | V                |
| $E_{AS}$       | Single Pulse Avalanche Energy (Note 2)                               |                                          | 580         | mJ               |
| $I_{AR}$       | Avalanche Current (Note 1)                                           |                                          | -16.5       | A                |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)                                 |                                          | 10          | mJ               |
| $dv/dt$        | Peak Diode Recovery $dv/dt$ (Note 3)                                 |                                          | -6.0        | V/ns             |
| $P_D$          | Power Dissipation                                                    | ( $T_C = 25^\circ\text{C}$ )             | 100         | W                |
|                |                                                                      | Derate above $25^\circ\text{C}$          | 0.67        |                  |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                              |                                          | -55 to +175 | $^\circ\text{C}$ |
| $T_L$          | Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds |                                          | 300         | $^\circ\text{C}$ |

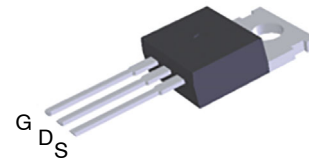
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature
2.  $L = 3.2$  mH,  $I_{AS} = -16.5$  A,  $V_{DD} = -25$  V,  $R_G = 25$  Ω, Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq -16.5$  A,  $di/dt \leq 300$  A/μs,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

| $V_{DS}$ | $R_{DS(on)}$ MAX | $I_D$ MAX |
|----------|------------------|-----------|
| -100 V   | 0.19 Ω @ -10 V   | -16.5 A   |

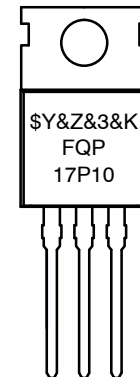


P-Channel MOSFET



TO-220-3LD  
CASE 340AT

### MARKING DIAGRAM



|          |                           |
|----------|---------------------------|
| \$Y      | = onsemi Logo             |
| &Z       | = Assembly Plant Code     |
| &3       | = Data Code (Year & Week) |
| &K       | = Lot Code                |
| FQP17P10 | = Specific Device Code    |

### ORDERING INFORMATION

| Device   | Package              | Shipping      |
|----------|----------------------|---------------|
| FQP17P10 | TO-220-3LD (Pb-Free) | 50 Units/Tube |

# FQP17P10

## THERMAL CHARACTERISTICS

| Symbol          | Parameter                                       | Ratings | Unit |
|-----------------|-------------------------------------------------|---------|------|
| $R_{\theta JC}$ | Maximum Thermal Resistance, Junction to Case    | 1.5     | °C/W |
| $R_{\theta CS}$ | Thermal Resistance, Case-to-Sink, Typ.          | 0.5     | °C/W |
| $R_{\theta JA}$ | Maximum Thermal Resistance, Junction to Ambient | 62.5    | °C/W |

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Unit |
|--------|-----------|----------------|------|------|------|------|
|--------|-----------|----------------|------|------|------|------|

### OFF CHARACTERISTICS

|                              |                                           |                                                                    |      |      |      |               |
|------------------------------|-------------------------------------------|--------------------------------------------------------------------|------|------|------|---------------|
| $BV_{DSS}$                   | Drain to Source Breakdown Voltage         | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$               | -100 | –    | –    | V             |
| $\Delta BV_{DSS}/\Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = -250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$ | –    | -0.1 | –    | V/°C          |
| $I_{DSS}$                    | Zero Gate Voltage Drain Current           | $V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$                      | –    | –    | -1   | $\mu\text{A}$ |
|                              |                                           | $V_{DS} = -80\text{ V}, T_C = 150^\circ\text{C}$                   | –    | –    | -10  |               |
| $I_{GSSF}$                   | Gate –Body Leakage Current, Forward       | $V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$                       | –    | –    | -100 | nA            |
| $I_{GSSR}$                   | Gate –Body Leakage Current, Reverse       | $V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$                        |      |      | 100  | nA            |

### ON CHARACTERISTICS

|              |                                   |                                                  |      |      |      |          |
|--------------|-----------------------------------|--------------------------------------------------|------|------|------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | -2.0 | –    | -4.0 | V        |
| $R_{DS(on)}$ | Static Drain–Source On–Resistance | $V_{GS} = -10\text{ V}, I_D = -8.25\text{ A}$    | –    | 0.14 | 0.19 | $\Omega$ |
| $g_{FS}$     | Forward Transconductance          | $V_{DS} = -40\text{ V}, I_D = -8.25\text{ A}$    | –    | 9.9  | –    | S        |

### DYNAMIC CHARACTERISTICS

|           |                              |                                                                  |   |     |      |    |
|-----------|------------------------------|------------------------------------------------------------------|---|-----|------|----|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$ | – | 850 | 1100 | pF |
| $C_{oss}$ | Output Capacitance           |                                                                  | – | 310 | 400  | pF |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                  | – | 100 | 130  | pF |

### SWITCHING CHARACTERISTICS

|              |                     |                                                                                   |   |     |     |    |
|--------------|---------------------|-----------------------------------------------------------------------------------|---|-----|-----|----|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = -50\text{ V}, I_D = -16.5\text{ A}, R_G = 25\text{ }\Omega$<br>(Note 4) | – | 17  | 45  | ns |
| $t_r$        | Turn–On Rise Time   |                                                                                   | – | 200 | 410 | ns |
| $t_{d(off)}$ | Turn–Off Delay Time |                                                                                   | – | 45  | 100 | ns |
| $t_f$        | Turn–Off Fall Time  |                                                                                   | – | 100 | 210 | ns |
| $Q_g$        | Total Gate Charge   | $V_{DS} = -80\text{ V}, I_D = -16.5\text{ A}, V_{GS} = -10\text{ V}$<br>(Note 4)  | – | 30  | 39  | nC |
| $Q_{gs}$     | Gate–Source Charge  |                                                                                   | – | 4.8 | –   | nC |
| $Q_{gd}$     | Gate–Drain Charge   |                                                                                   | – | 17  | –   | nC |

### DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

|          |                                                       |                                                                                 |   |      |       |               |
|----------|-------------------------------------------------------|---------------------------------------------------------------------------------|---|------|-------|---------------|
| $I_S$    | Maximum Continuous Drain–Source Diode Forward Current |                                                                                 | – | –    | -16.5 | A             |
| $I_{SM}$ | Maximum Pulsed Drain–Source Diode Forward Current     |                                                                                 | – | –    | -66   | A             |
| $V_{SD}$ | Drain–Source Diode Forward Voltage                    | $V_{GS} = 0\text{ V}, I_S = -16.5\text{ A}$                                     | – | –    | -4.0  | V             |
| $t_{rr}$ | Reverse Recovery Time                                 | $V_{GS} = 0\text{ V}, I_S = -16.5\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$ | – | 120  | –     | ns            |
| $Q_{rr}$ | Reverse Recovery Charge                               |                                                                                 | – | 0.52 | –     | $\mu\text{C}$ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

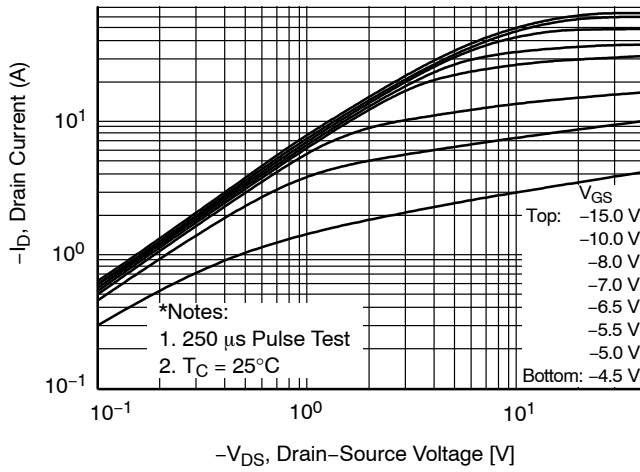


Figure 1. On-Region Characteristics

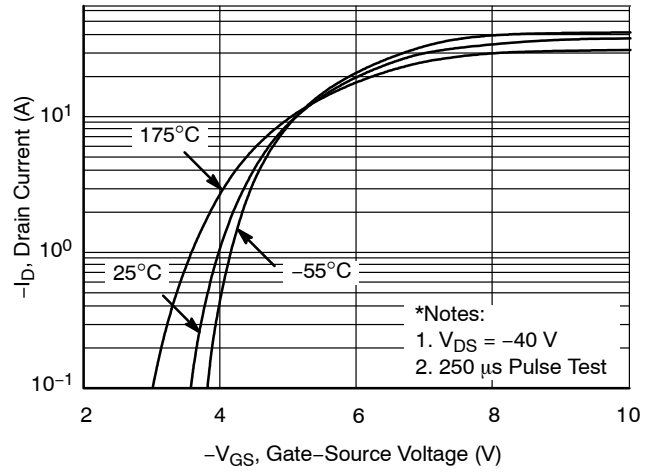


Figure 2. Transfer Characteristics

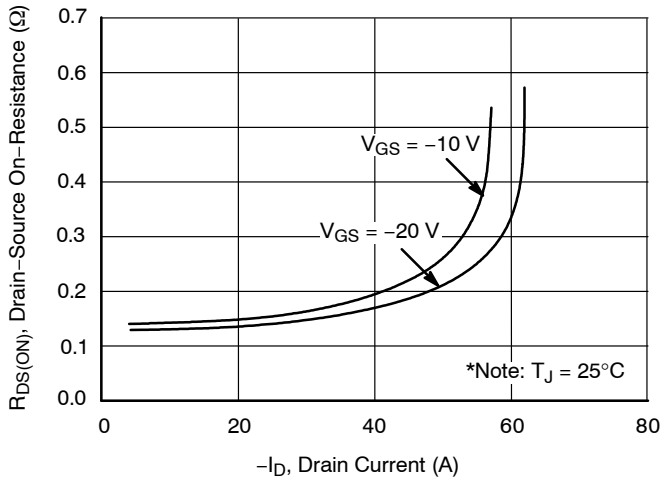


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

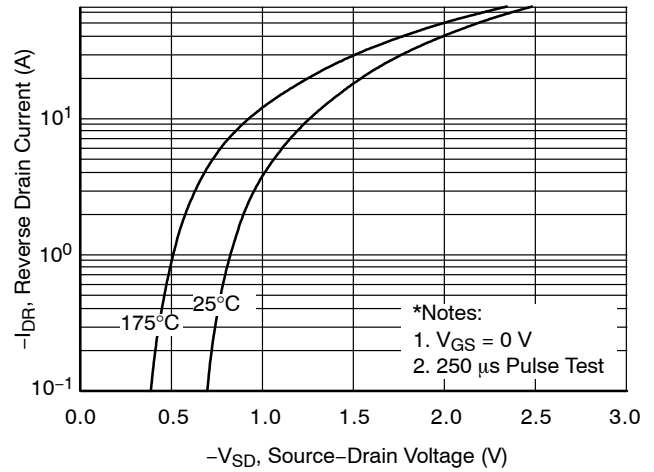


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

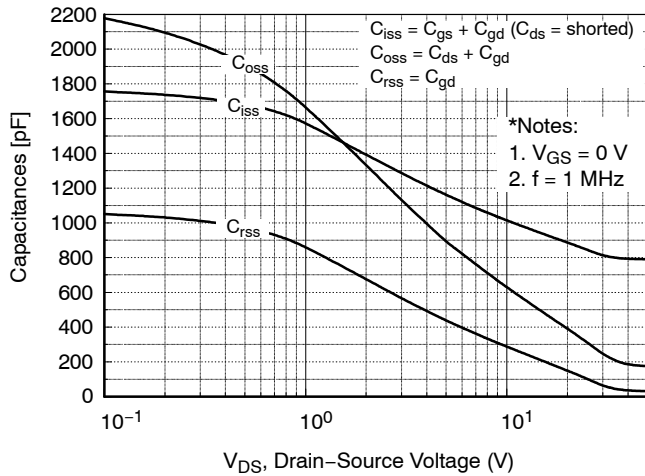


Figure 5. Capacitance Characteristics

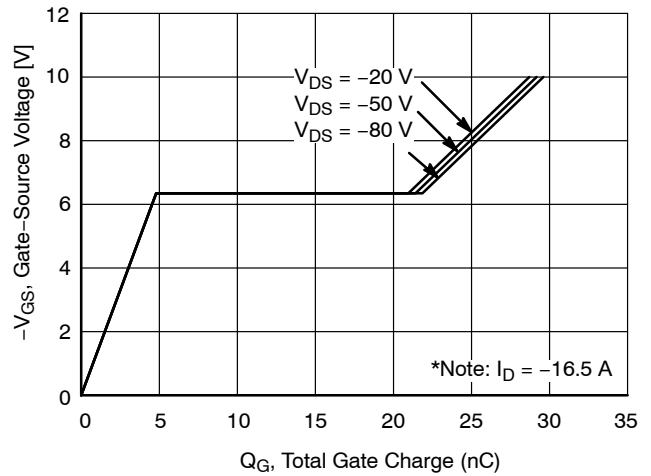
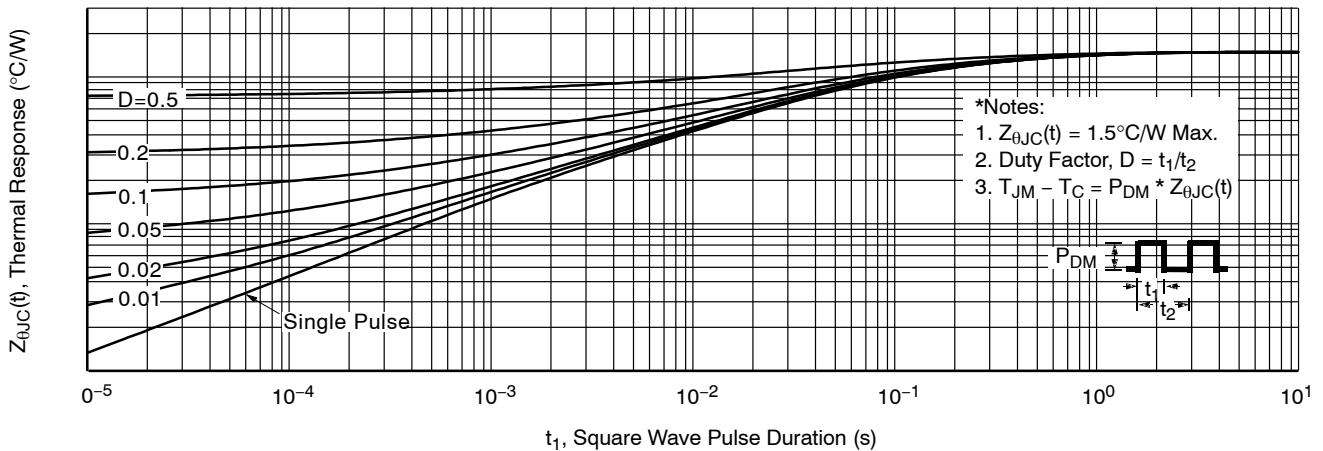
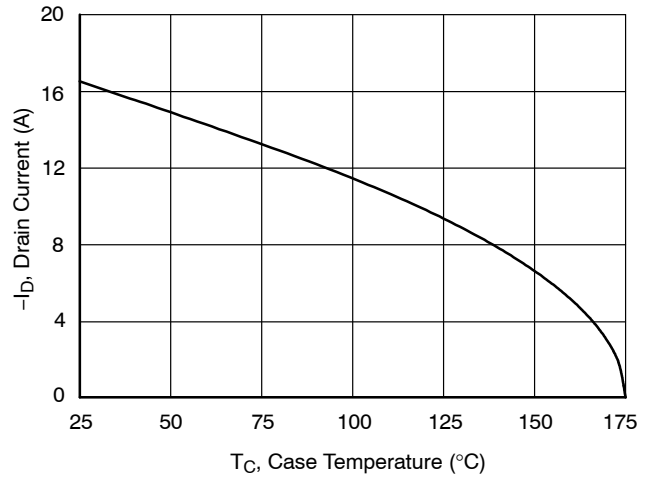
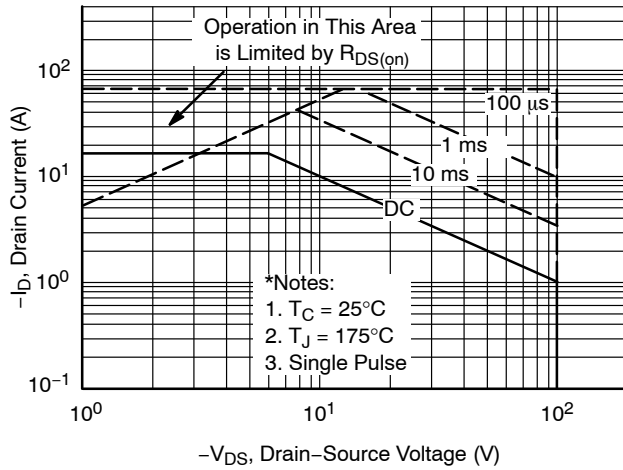
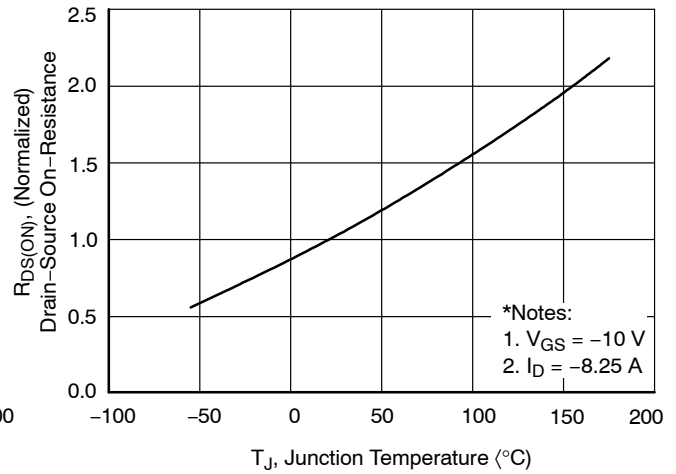
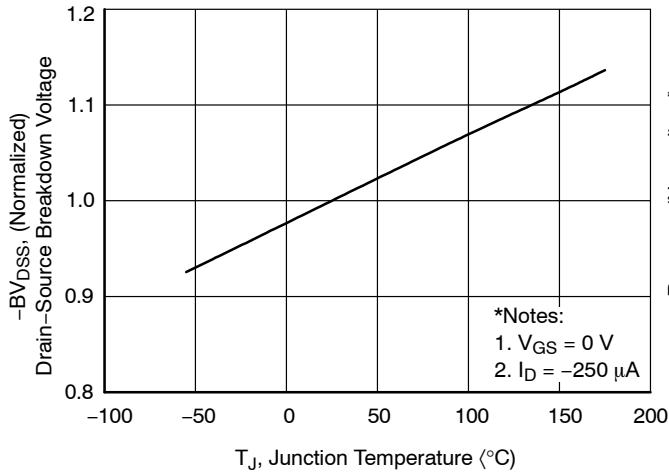


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS (continued)



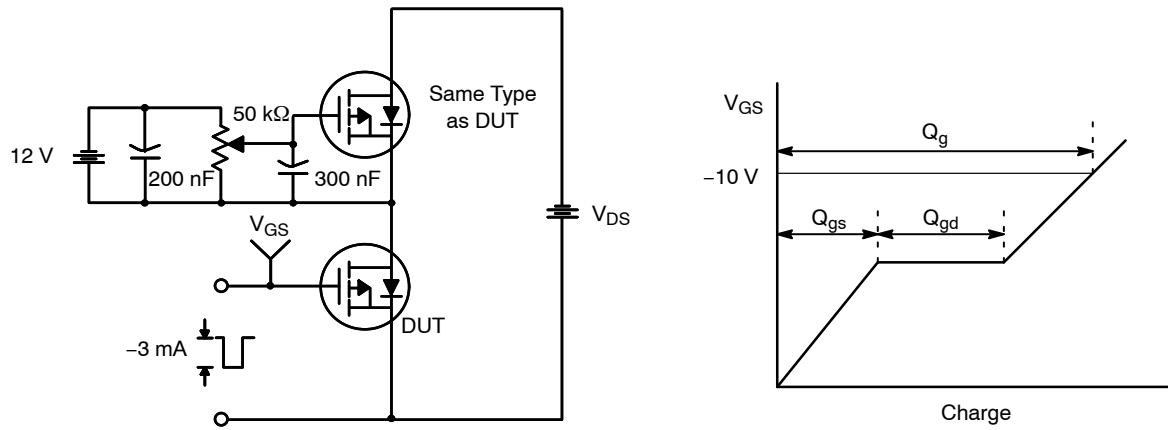


Figure 12. Gate Charge Test Circuit & Waveform

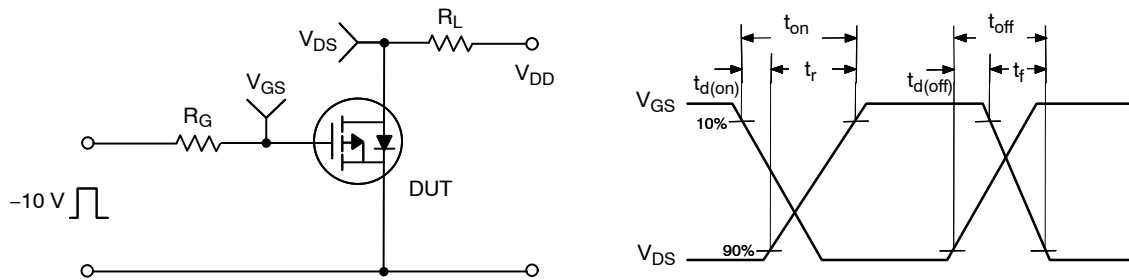


Figure 13. Resistive Switching Test Circuit & Waveforms

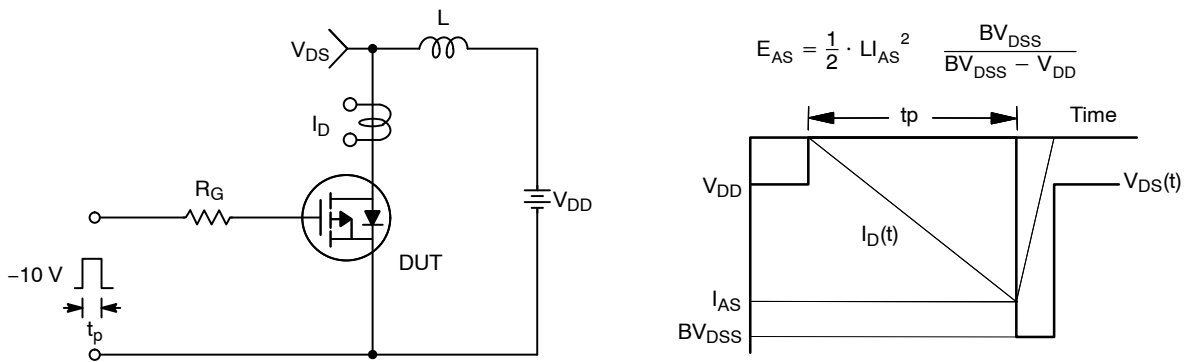
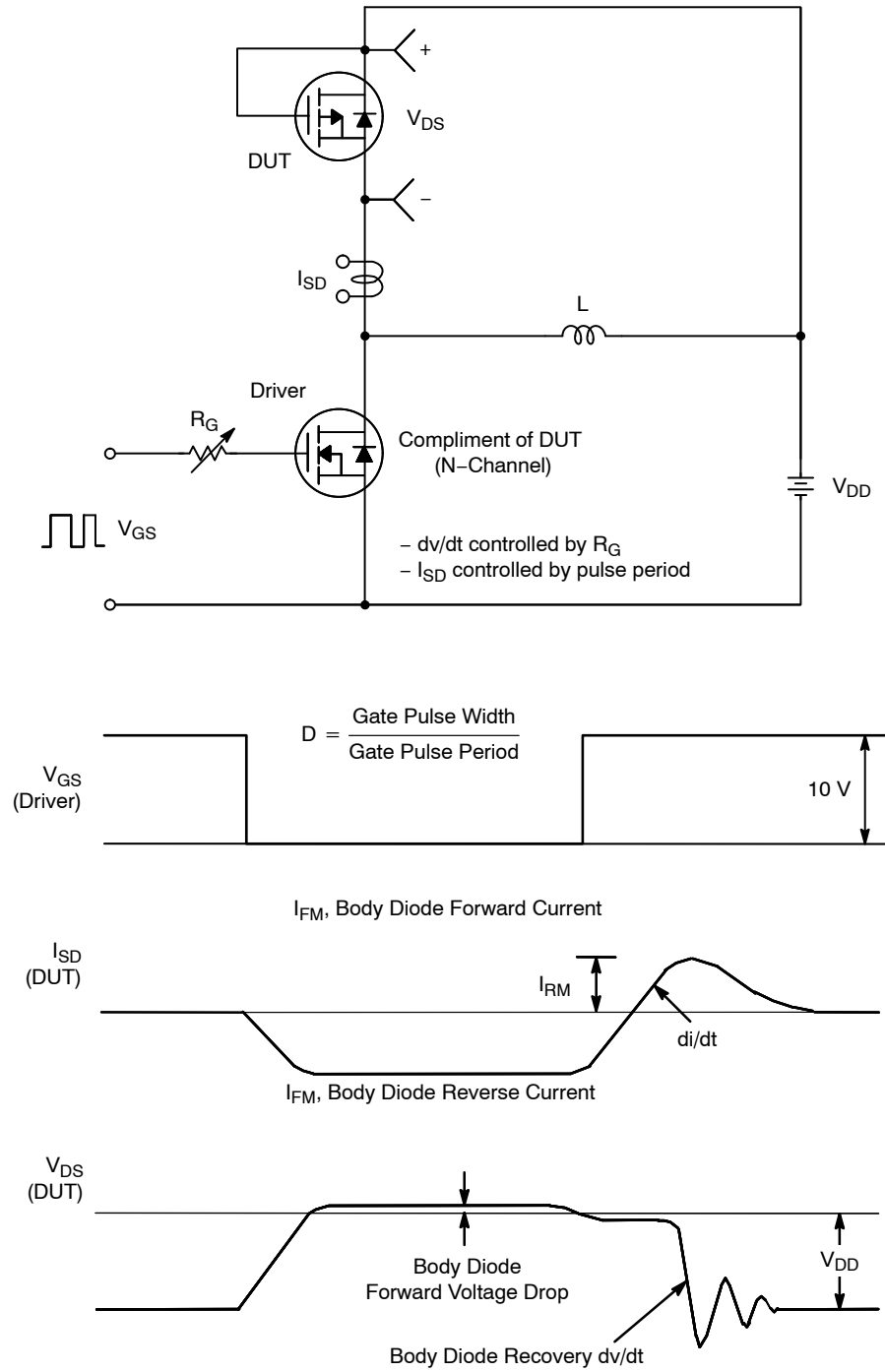


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

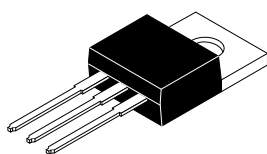
# FQP17P10



**Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms**

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

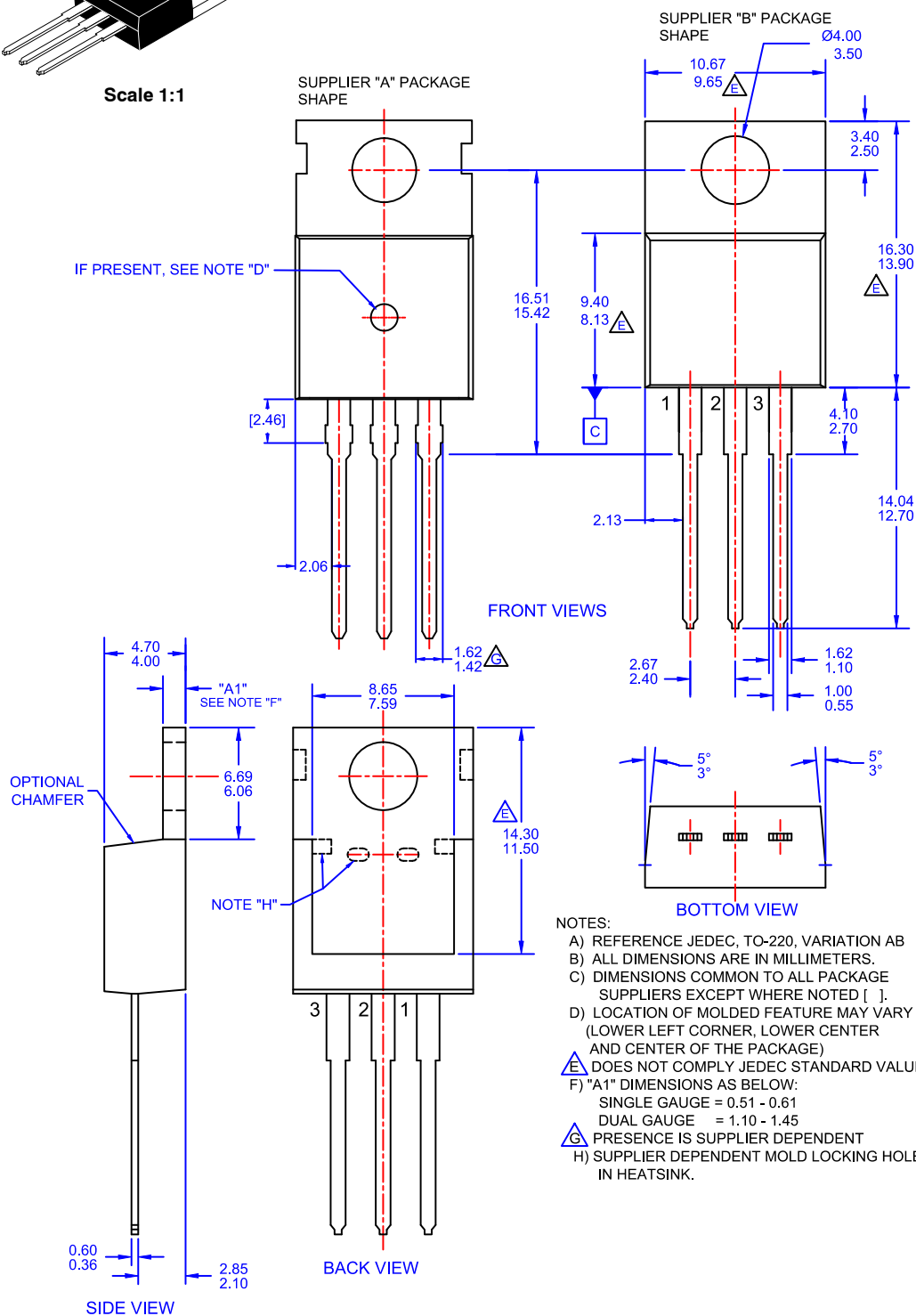
ON Semiconductor®



Scale 1:1

## TO-220-3LD CASE 340AT ISSUE A

DATE 03 OCT 2017



### NOTES:

- A) REFERENCE JEDEC, TO-220, VARIATION AB
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
- D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
- E) DOES NOT COMPLY JEDEC STANDARD VALUE.
- F) "A1" DIMENSIONS AS BELOW:  
SINGLE GAUGE = 0.51 - 0.61  
DUAL GAUGE = 1.10 - 1.45
- G) PRESENCE IS SUPPLIER DEPENDENT
- H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

|                  |             |                                                                                                                                                                                     |
|------------------|-------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| DOCUMENT NUMBER: | 98AON13818G | Electronic versions are uncontrolled except when accessed directly from the Document Repository.<br>Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| DESCRIPTION:     | TO-220-3LD  | PAGE 1 OF 1                                                                                                                                                                         |

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at  
[www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)